

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Typ.)
- 20	0.104 at V _{GS} = - 4.5 V	- 3.8	6 nC
	0.148 at V _{GS} = - 2.5 V	- 3.2	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

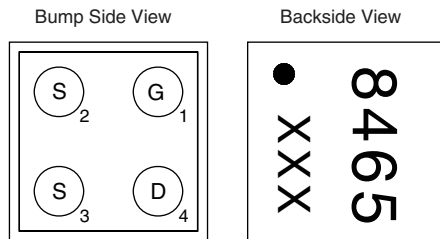


RoHS
COMPLIANT
HALOGEN
FREE

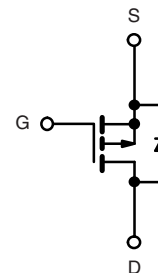
APPLICATIONS

- Load Switches, Battery Switches and Charger Switches in Portable Device Applications
- DC/DC Converters

MICRO FOOT



Device Marking: 8465
xxx = Date/Lot Traceability Code



P-Channel MOSFET

Ordering Information: Si8465DB-T2-E1 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 20	V
Gate-Source Voltage	V _{GS}	± 12	
Continuous Drain Current (T _J = 150 °C)	I _D	T _A = 25 °C	- 3.8 ^a
		T _A = 70 °C	- 3 ^a
		T _A = 25 °C	- 2.5 ^b
		T _A = 70 °C	- 2.0 ^b
Pulsed Drain Current	I _{DM}	- 15	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	- 0.65 ^b
Maximum Power Dissipation	P _D	T _A = 25 °C	1.8 ^a
		T _A = 70 °C	1.1 ^a
		T _A = 25 °C	0.78 ^b
		T _A = 70 °C	0.5 ^b
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Package Reflow Conditions ^c	VPR	260	
	IR/Convection	260	

Notes:

- Surface mounted on 1" x 1" FR4 board with full copper, t = 10 s.
- Surface mounted on 1" x 1" FR4 board with minimum copper, t = 10 s.
- Refer to IPC/JEDEC (J-STD-020C), no manual or hand soldering.
- In this document, any reference to case represents the body of the MICRO FOOT device and foot is the bump.
- Based on T_A = 25 °C.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, b}	$t = 10 \text{ s}$	55	70	°C/W
Maximum Junction-to-Ambient ^{c, d}	$t = 10 \text{ s}$	125	160	

Notes:

- a. Surface mounted on 1" x 1" FR4 board with full copper.
 b. Maximum under steady state conditions is 100 °C/W.
 c. Surface mounted on 1" x 1" FR4 board with minimum copper.
 d. Maximum under steady state conditions is 190 °C/W.

SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted

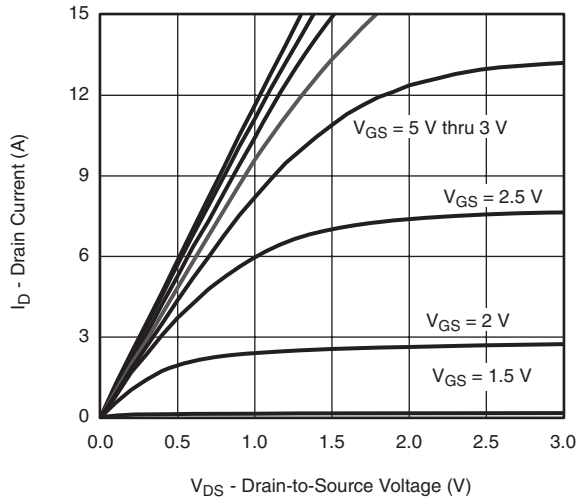
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250 \mu\text{A}$		-12		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		2.8			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-0.6		-1.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 70 \text{ °C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -1.5 \text{ A}$		0.086	0.104	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A}$		0.122	0.148	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10 \text{ V}, I_D = -1.5 \text{ A}$		7		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		450		pF
Output Capacitance	C_{oss}		125			
Reverse Transfer Capacitance	C_{rss}		95			
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -1 \text{ A}$		12	18	nC
		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = 1 \text{ A}$		6	9	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = 1 \text{ A}$		0.85		nC
Gate-Drain Charge	Q_{gd}		2.2			
Gate Resistance	R_g		$V_{GS} = -0.1 \text{ V}, f = 1 \text{ MHz}$		7.5	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		20	30	ns
Rise Time	t_r		20	30		
Turn-Off Delay Time	$t_{d(off)}$		25	40		
Fall Time	t_f		10	15		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		7	15	ns
Rise Time	t_r		10	15		
Turn-Off Delay Time	$t_{d(off)}$		25	40		
Fall Time	t_f		10	15		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_A = 25 \text{ °C}$			-1.5	A
Pulse Diode Forward Current	I_{SM}				-15	
Body Diode Voltage	V_{SD}	$I_S = -1 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -1 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}, T_J = 25 \text{ °C}$		20	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}		10	20	nC	
Reverse Recovery Fall Time	t_a		10		ns	
Reverse Recovery Rise Time	t_b		10			

Notes:

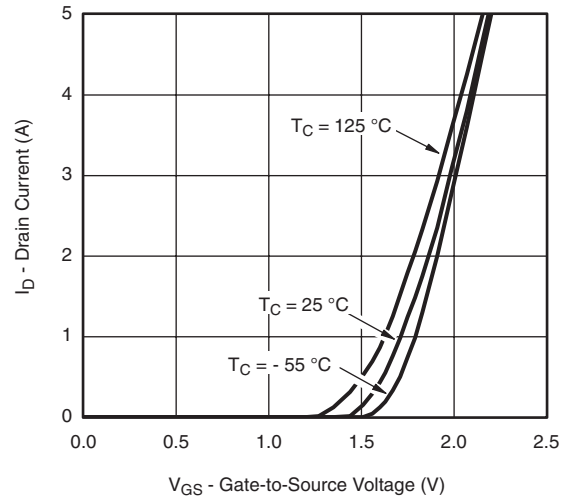
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

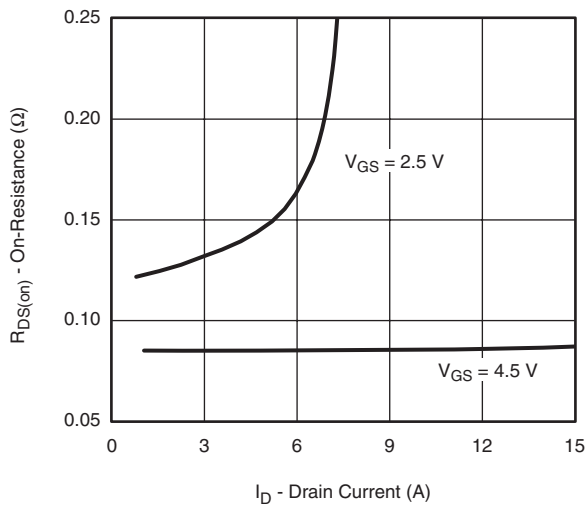
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



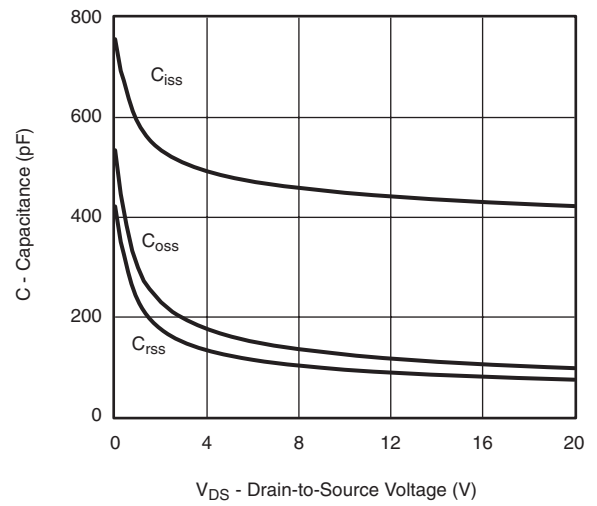
Output Characteristics



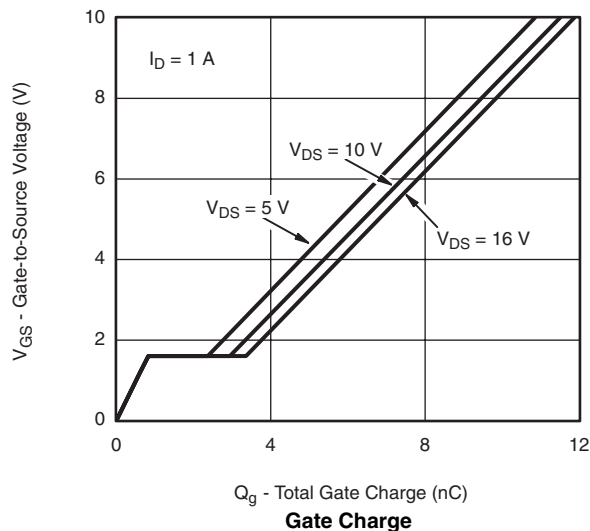
Transfer Characteristics



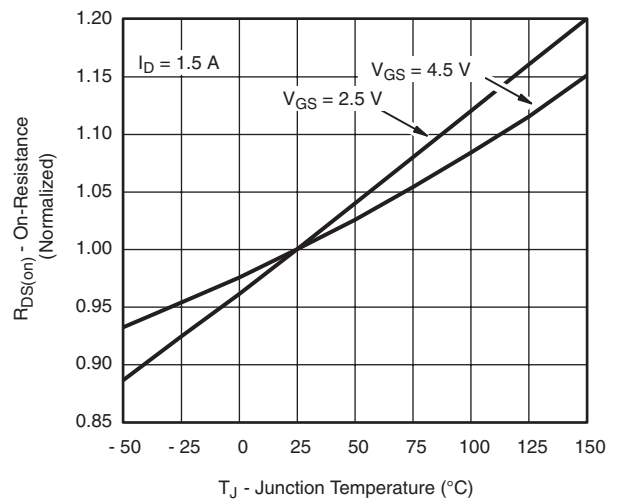
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

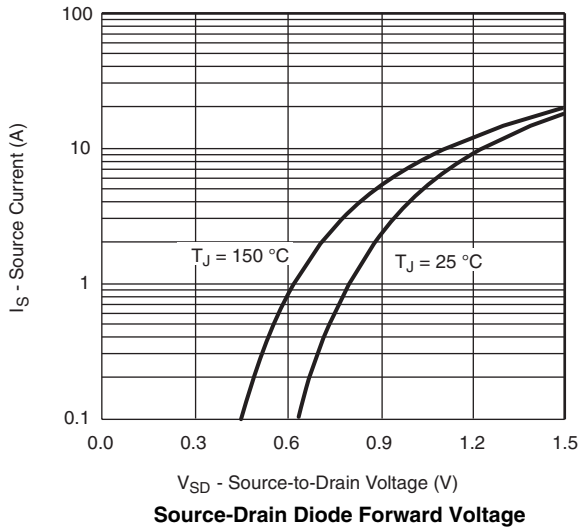


Gate Charge

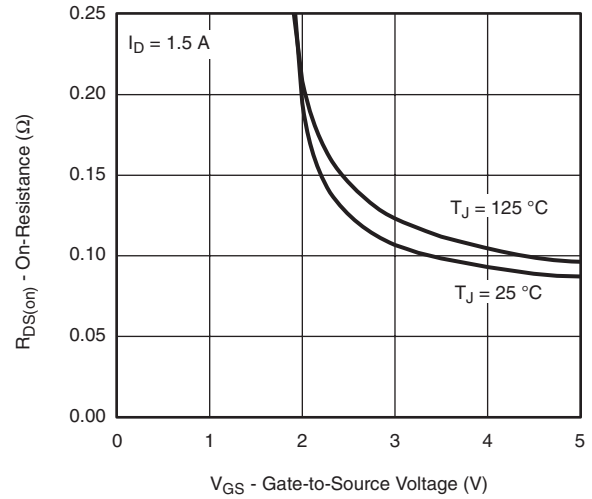


On-Resistance vs. Junction Temperature

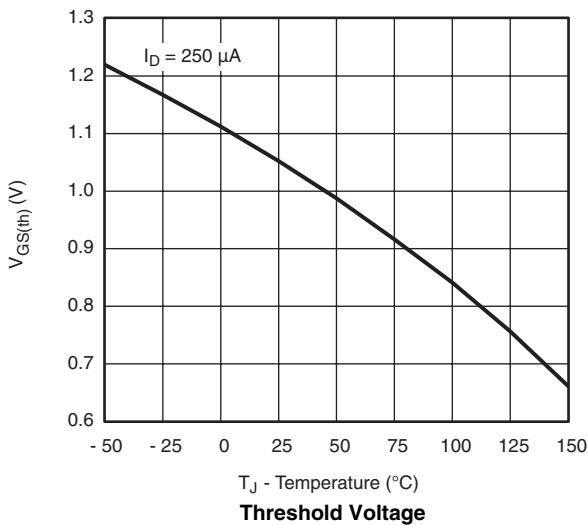
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



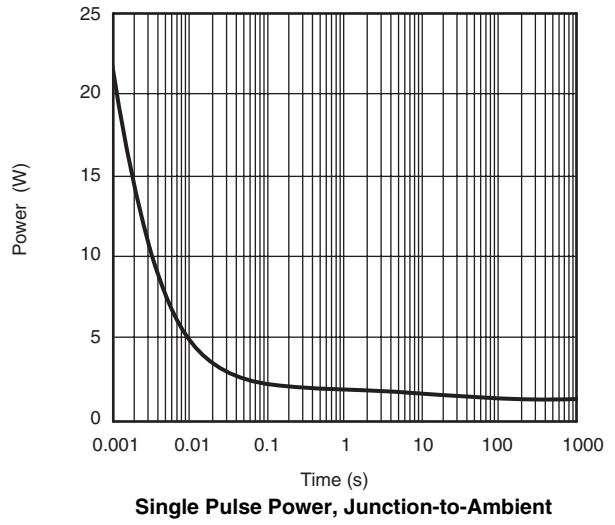
Source-Drain Diode Forward Voltage



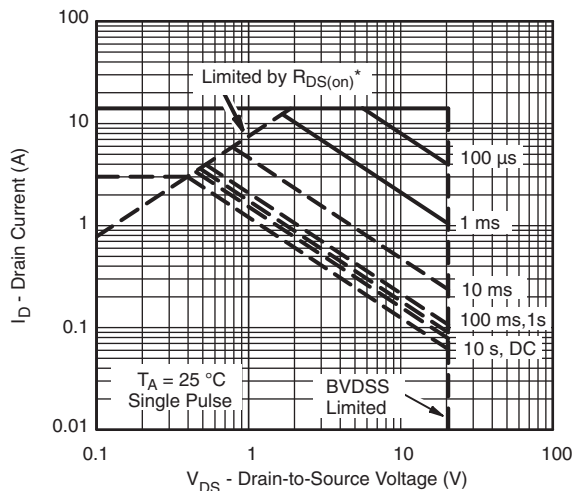
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



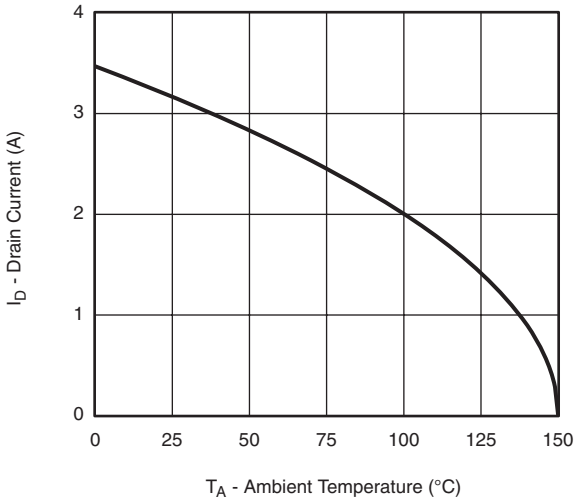
Single Pulse Power, Junction-to-Ambient



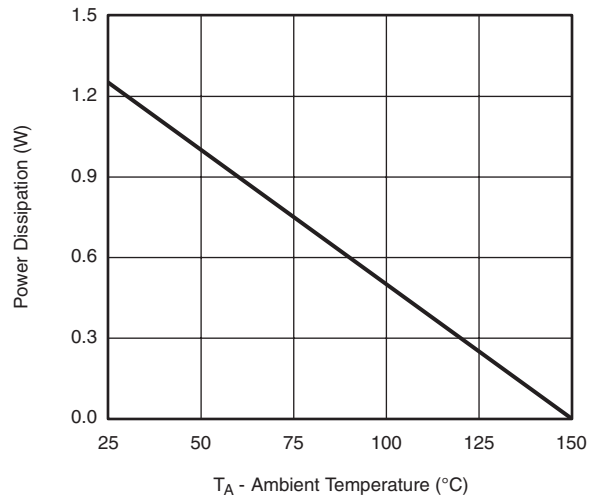
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*

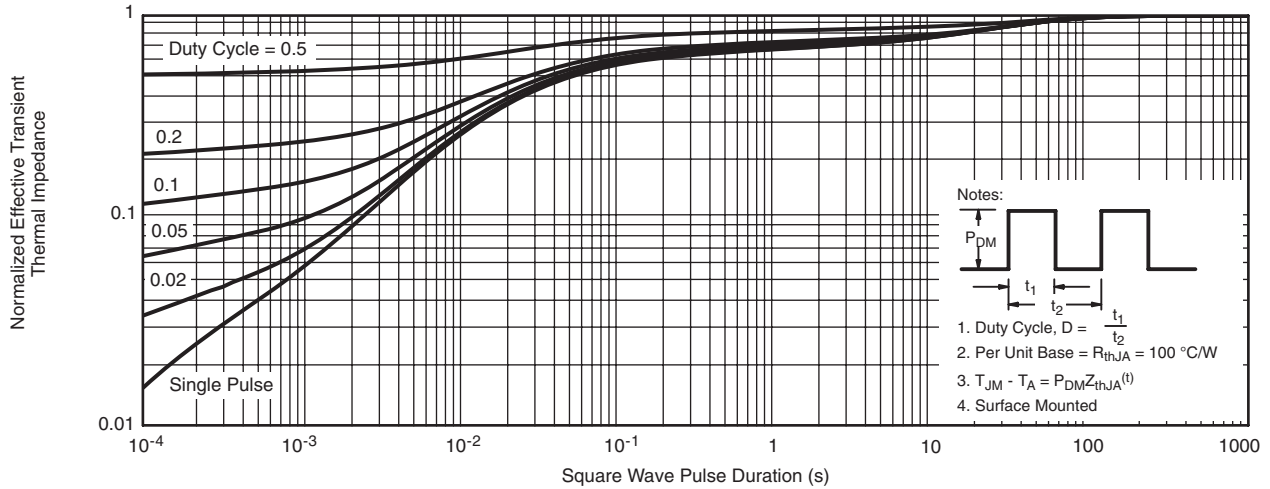


Power Derating

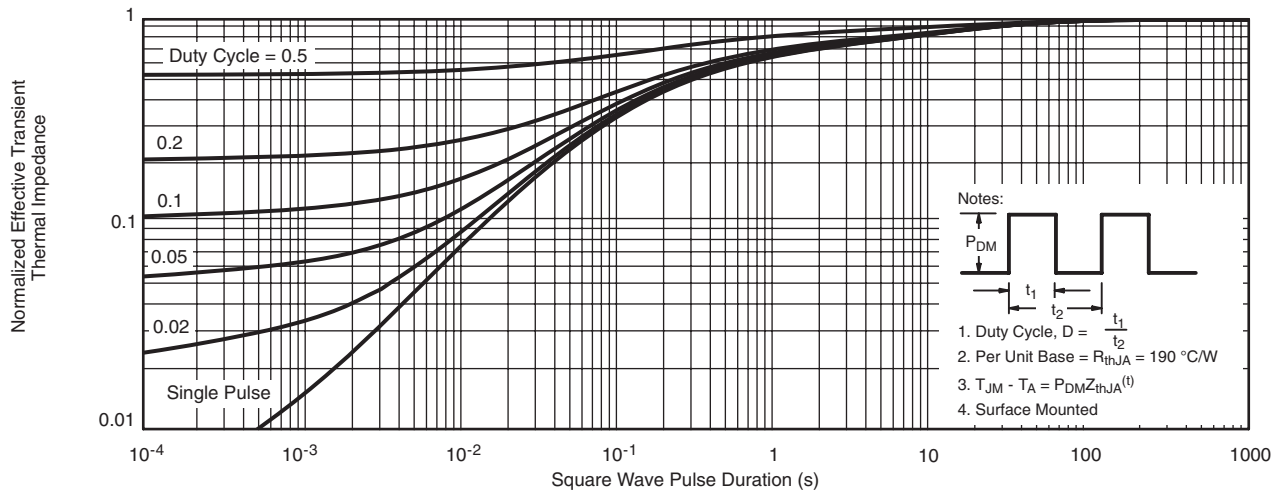
Note:
When Mounted on 1" x 1" FR4 with Full Copper.

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



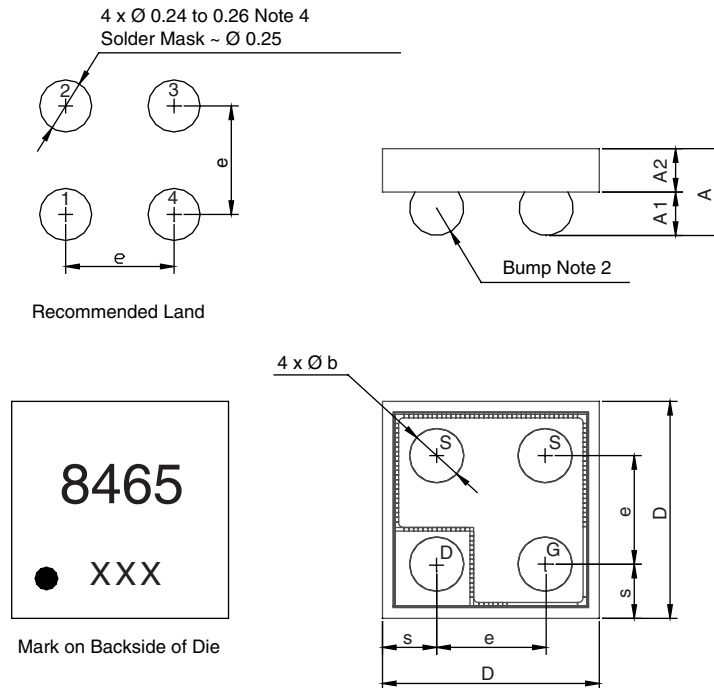
Normalized Thermal Transient Impedance, Junction-to-Ambient (1" x 1" FR4 Board with Full Copper)



Normalized Thermal Transient Impedance, Junction-to-Ambient (1" x 1" FR4 Board with Minimum Copper)

PACKAGE OUTLINE

MICRO FOOT: 4-BUMP (2 x 2, 0.5 mm PITCH)



Notes (Unless otherwise specified):

1. All dimensions are in millimeters.
2. Four (4) solder bumps are lead (Pb)-free 95.5Sn/3.8Ag/0.7Cu with diameter \varnothing 0.30 mm to 0.32 mm.
3. Backside surface is coated with a Ti/Ni/Ag layer.
4. Non-solder mask defined copper landing pad.
5. • is location of pin 1.

Dim.	Millimeters ^a			Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	0.462	0.505	0.548	0.0181	0.0198	0.0215
A₁	0.220	0.250	0.280	0.0086	0.0098	0.0110
A₂	0.242	0.255	0.268	0.0095	0.0100	0.0105
b	0.300	0.310	0.320	0.0118	0.0122	0.0126
e	0.500			0.0197		
s	0.230	0.250	0.270	0.0090	0.0098	0.0106
D	0.920	0.960	1.000	0.0362	0.0378	0.0394

Notes:

- a. Use millimeters as the primary measurement.

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